

DUAL D TYPE FLIP FLOP WITH PRESET AND CLEAR

- HIGH SPEED
- $f_{MAX} = 71 \text{ MHz} (TYP.) \text{ AT V}_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 2 \mu A \text{ (MAX.)} \text{ AT } T_A = 25 \text{ °C}$
- HIGH NOISE IMMUNITY

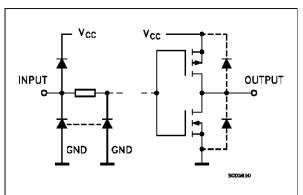
 VNIH = VNIL = 28 % VCC (MIN.)
- OUTPUT DRIVE CAPABILITY 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE | I_{OH} | = I_{OL} = 4 mA (MIN.)
- BALANCED PROPÄGATÍON DELAYS tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS74

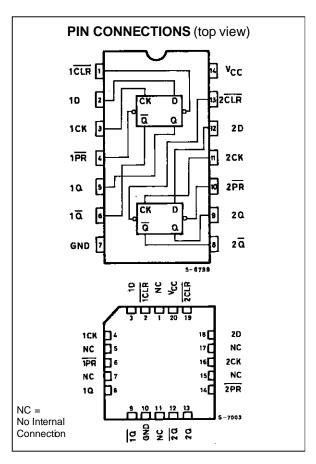
B1R F1R (Ceramic Package) M1R (C1R (Chip Carrier)) ORDER CODES: M54HC74F1R M74HC74M1R M74HC74B1R M74HC74C1R

DESCRIPTION

The M54/74HC74 is a high speed CMOS DUAL D TYPE FLOP WITH PRESET AND CLEAR fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. A signal on the D INPUT is transferred to the Q OUTPUT during the positive going transition of the clock pulse. CLEAR and PRESET are independent of the clock and accomplished by a low on the appropriate input. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT





October 1992 1/11

TRUTH TABLE

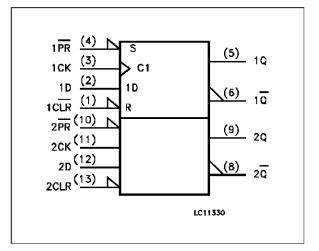
	INP	UTS		OUT	PUTS	FUNCTION
CLR	PR	D	СК	Q	Q	TONCTION
L	Н	Х	Х	L	Н	CLEAR
Н	L	Х	X	Н	L	PRESET
L	L	Х	Х	Н	Н	
Н	Н	L		L	Н	
Н	Н	Н		Н	L	
Н	Н	Х	1	Qn	Qn	NO CHANGE

X: Don't Care

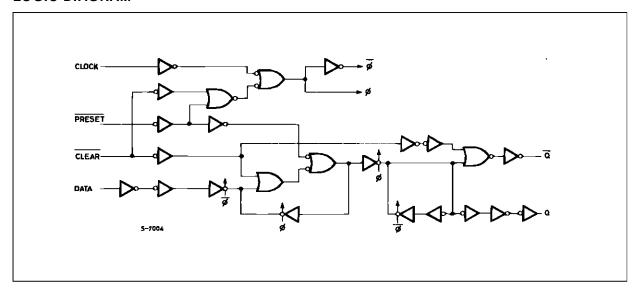
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 13	1 <u>CLR,</u> 2CLR	Asyncronous Reset - Direct Input
2, 12	1D, 2D	Data Inputs
3, 11	1CK, 2CK	Clock Input (LOW-to-HIGH, Edge- Triggered)
4, 10	1PR, 2PR	Asyncronous Set - Direct Input
5, 9	1Q, 2Q	True Flip-Flop Outpus
6, 8	1\overline{Q}, 2\overline{Q}	Complement Flip-Flop Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
Io	DC Output Source Sink Current Per Output Pin	± 25	mA
Icc or Ignd	DC Vcc or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: \cong 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V _{CC}	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T_op	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	°C °C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V	0 to 1000	ns
		V _{CC} = 4.5 V	0 to 500	
		V _{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

		Test Conditions		Value								
Symbol	Parameter	V _{CC}				_A = 25 ^c C and 7			85 °C HC	-55 to 54	125 °C HC	Unit
		(۷)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
V_{OH}	High Level	2.0	Vı =		1.9	2.0		1.9		1.9		\
	Output Voltage	4.5	VI –		4.4	4.5		4.4		4.4		
		6.0	or		5.9	6.0		5.9		5.9		V
		4.5	V _{IL}	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		lo=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output	2.0	V _I =			0.0	0.1		0.1		0.1	
	Voltage	4.5	VI – VIH	I _O = 20 μA		0.0	0.1		0.1		0.1	
		6.0	or			0.0	0.1		0.1		0.1	V
		4.5	VIL	I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
lı	Input Leakage Current	6.0	V _I = '	V _{CC} or GND			±0.1		±1		±1	μΑ
Icc	Quiescent Supply Current	6.0	V _I = '	V _{CC} or GND			2		20		40	μА

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

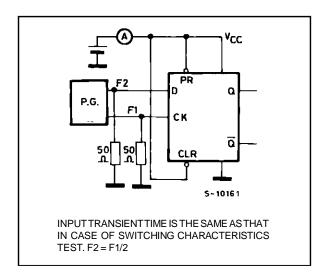
		Te	est Conditions				Value				
Symbol	Parameter	Vcc		T _A = 25 °C -40 to 85 °C 54HC and 74HC 74HC					-55 to 54	Unit	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH}	Output Transition	2.0			30	75		95		110	
t _{THL}	Time	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{PLH}	Propagation	2.0			48	150		190		225	
t _{PHL}	Delay Time	4.5			16	30		38		45	ns
	(CLOCK - Q)	6.0			13	26		32		38	
t _{PLH}	Propagation	2.0			51	150		190		225	
t _{PHL}	Delay Time	4.5			17	30		38		45	ns
	(CL, PR - Q)	6.0			15	26		32		38	
f _{MAX} Maximum Clock	2.0		6.2	21		5		4.2			
	Frequency	4.5		31	63		25		21		MHz
		6.0		37	67		30		25		
t _{W(H)}	Minimum Pulse	2.0			18	75		95		110	ns
t _{W(L)}	Width	4.5			6	15		19		22	
	(CLOCK)	6.0			6	13		16		19	
t _{W(L)}	Minimum Pulse	2.0			21	75		95		110	
	Width	4.5			7	15		19		22	ns
	(CL, PR)	6.0			6	13		16		19	
ts	Minimum Set-up	2.0			15	75		95		110	
	Time	4.5			4	15		19		22	ns
		6.0			3	13		16		19	
t _h	Minimum Hold	2.0				0		0		0	
	Time	4.5				0		0		0	ns
		6.0				0		0		0	
t _{REM} Minimum	2.0			0	25		30		35		
	Removal Time	4.5			0	5		6		7	ns
	(CL, PR)	6.0			0	4		5		6	
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				34						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/2$ (per FLIP/FLOP)

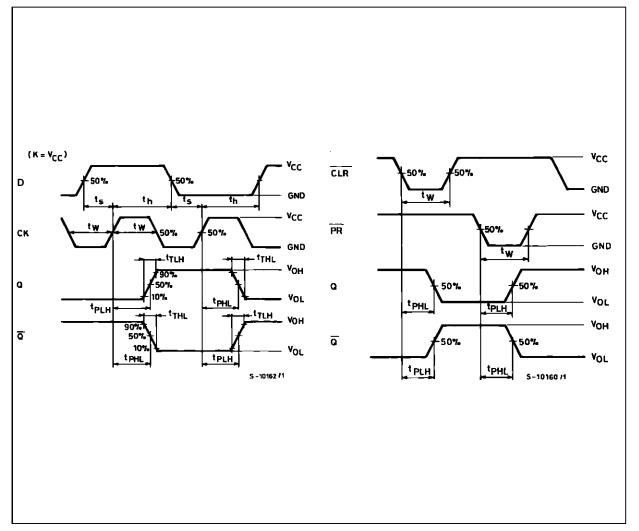
SWITCHING CHARACTERISTICS TEST WAVEFORM

Vc¢ PR 50% GND v_{CC} ÇK 30% GND ¹REM-^УОН VOL $v_{\rm CC}$ 50 % CLR 5-10169/1 GND ACC СК 50% GND t_{REM} νон ۵ VOL 5-10164

TEST CIRCUIT Icc (Opr.)

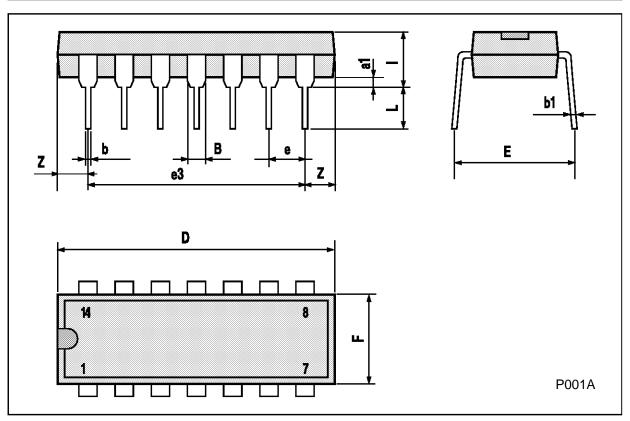


SWITCHING CHARACTERISTICS TEST WAVEFORM (K = Vcc)



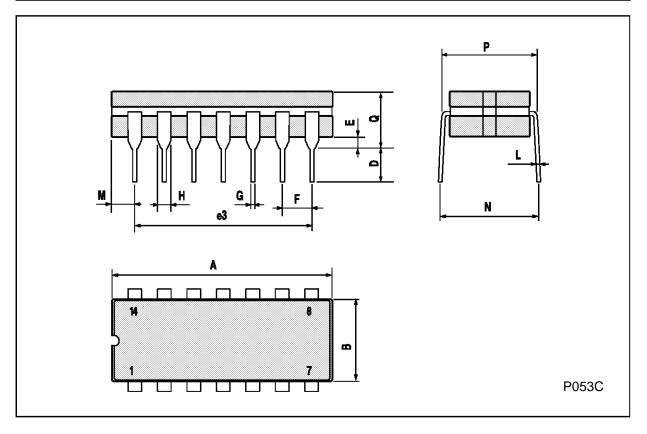
Plastic DIP14 MECHANICAL DATA

DIM.		mm		inch				
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	1.39		1.65	0.055		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		15.24			0.600			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z	1.27		2.54	0.050		0.100		



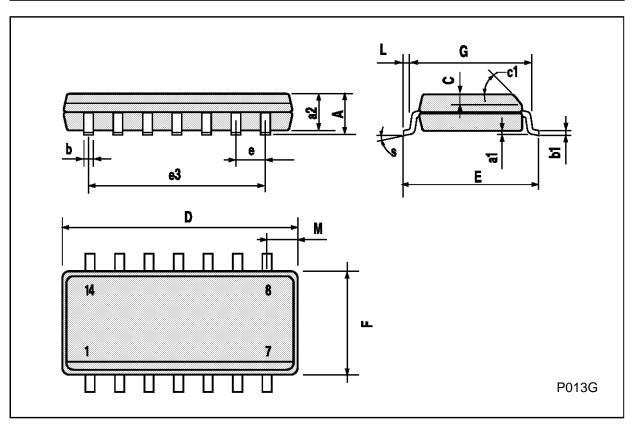
Ceramic DIP14/1 MECHANICAL DATA

DIM.		mm			inch	
J	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			20			0.787
В			7.0			0.276
D		3.3			0.130	
Е	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
Н	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
М	1.52		2.54	0.060		0.100
N			10.3			0.406
Р	7.8		8.05	0.307		0.317
Q			5.08			0.200



SO14 MECHANICAL DATA

DIM.		mm		inch				
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	8.55		8.75	0.336		0.344		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		7.62			0.300			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.68			0.026		
S			8° (ı	max.)				



PLCC20 MECHANICAL DATA

DIM.		mm		inch				
Diiii.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А	9.78		10.03	0.385		0.395		
В	8.89		9.04	0.350		0.356		
D	4.2		4.57	0.165		0.180		
d1		2.54			0.100			
d2		0.56			0.022			
E	7.37		8.38	0.290		0.330		
е		1.27			0.050			
e3		5.08			0.200			
F		0.38			0.015			
G			0.101			0.004		
М		1.27			0.050			
M1		1.14			0.045			



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